MMBT489LT1G

High Current Surface Mount NPN Silicon Switching Transistor for Load Management in Portable Applications

Features

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V _{CBO}	50	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	I _C	1.0	Α
Collector Current – Peak	I _{CM}	2.0	Α

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) @T _A = 25°C Derate above 25°C	P _D	310 2.5	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	403	°C/W
Total Device Dissipation (Note 2) @T _A = 25°C Derate above 25°C	P _D	710 5.7	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	176	°C/W
Total Device Dissipation (Single Pulse < 10 s)	P _{Dsingle}	575	mW
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

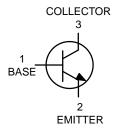
- 1. FR-4 @ Minimum Pad
- 2. FR-4 @ 1.0 X 1.0 inch Pad



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30 VOLTS, 2.0 AMPERES NPN TRANSISTOR





SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



N3 = Specific Device Code

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

	Device	Package	Shipping [†]
M	IMBT489LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT489LT1G

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ noted)$

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•	•	•	
Collector – Emitter Breakdown Voltage $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _(BR) CEO	30	-	Vdc
Collector–Base Breakdown Voltage (I _C = 0.1 mAdc, I _E = 0)	V _(BR) CBO	50	-	Vdc
Emitter – Base Breakdown Voltage $(I_E = 0.1 \text{ mAdc}, I_C = 0)$	V _{(BR)EBO}	5.0	-	Vdc
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)	І _{СВО}	-	0.1	μAdc
Collector–Emitter Cutoff Current (V _{CES} = 30 Vdc)	ICES	-	0.1	μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc)	I _{EBO}	-	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) (I _C = 50 mA, V _{CE} = 5.0 V) (I _C = 0.5 A, V _{CE} = 5.0 V) (I _C = 1.0 A, V _{CE} = 5.0 V)	h _{FE}	300 300 200	900 -	
Collector – Emitter Saturation Voltage (Note 3)	V _{CE} (sat)	- - -	0.200 0.125 0.075	V
Base-Emitter Saturation Voltage (Note 3) (I _C = 1.0 A, I _B = 0.1 A)	V _{BE(sat)}	-	1.1	V
Base – Emitter Turn–on Voltage (Note 3) ($I_C = 1.0 \text{ mA}, V_{CE} = 2.0 \text{ V}$)	V _{BE(on)}	-	1.1	V
Cutoff Frequency ($I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz}$	f⊤	100	-	MHz
Output Capacitance (f = 1.0 MHz)	C _{obo}	_	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 μ sec, Duty Cycle $\leq 2\%$

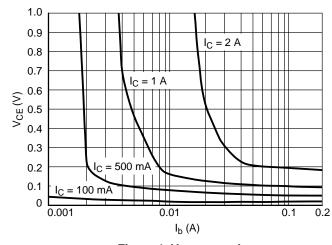


Figure 1. V_{CE} versus I_b

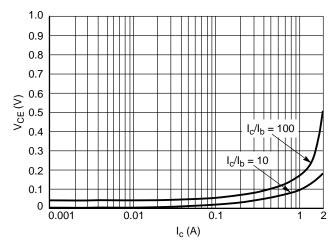


Figure 2. V_{CE} versus I_c

MMBT489LT1G

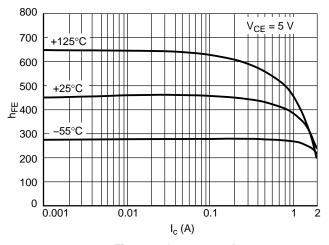


Figure 3. h_{FE} versus I_c

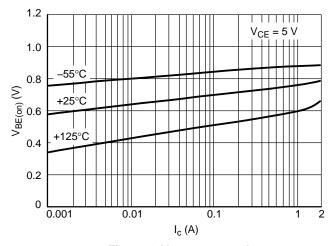


Figure 4. $V_{BE(on)}$ versus I_c

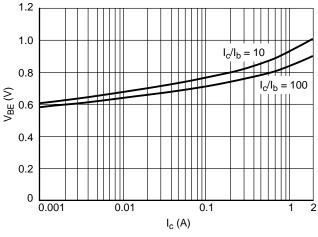


Figure 5. $V_{\text{BE(sat)}}$ versus I_{c}

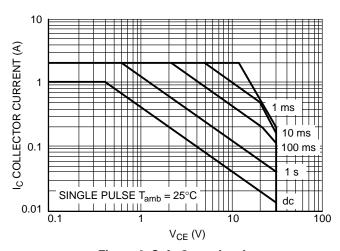


Figure 6. Safe Operating Area

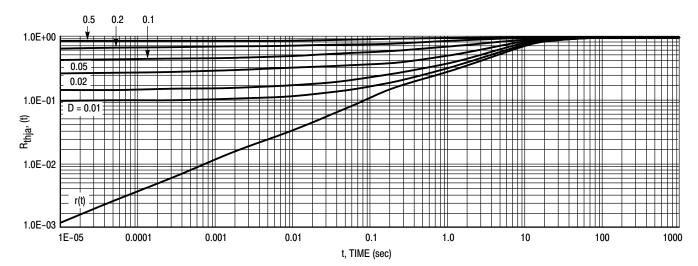


Figure 7. Normalized Thermal Response



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	ANODE	3. GATE	ANODE

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
CATHODE	CATHODE	2. ANODE	CATHODE	2. ANODE	ANODE
ANODE	CATHODE	CATHODE	ANODE	CATHODE-ANOD	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	NO CONNECTION

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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